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What Are <u>Embedded - Microcontrollers -</u> <u>Application Specific</u>?

Application charific microcontrollars are analyzared to

Details

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Product Status	Not For New Designs
Applications	Automotive
Core Processor	ARM® Cortex®-M3
Program Memory Type	FLASH (64kB)
Controller Series	-
RAM Size	6K x 8
Interface	LIN, SSI, UART
Number of I/O	10
Voltage - Supply	5.5V ~ 28V
Operating Temperature	-40°C ~ 150°C
Mounting Type	Surface Mount
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	PG-VQFN-48-31
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/tle9877qxa20xuma2

Email: info@E-XFL.COM

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TLE9877QXA20



Overview

Table 1 Acronyms										
Acronyms	Name									
PCU	Power Control Unit									
PD	Pull Down									
PGU	Power supply Generation Unit									
PLL	Phase Locked Loop									
PPB	Private Peripheral Bus									
PU	Pull Up									
PWM	Pulse Width Modulation									
RAM	Random Access Memory									
RCU	Reset Control Unit									
RMU	Reset Management Unit									
ROM	Read Only Memory									
SCU-DM	System Control Unit - Digital Modules									
SCU-PM	System Control Unit - Power Modules									
SFR	Special Function Register									
SOW	Short Open Window (for WDT)									
SPI	Serial Peripheral Interface									
SSC	Synchronous Serial Channel									
STM	Store Instruction									
SWD	ARM Serial Wire Debug									
TCCR	Temperature Compensation Control Register									
TMS	Test Mode Select									
TSD	Thermal Shut Down									
UART	Universal Asynchronous Receiver Transmitter									
VBG	Voltage reference Band Gap									
VCO	Voltage Controlled Oscillator									
VPRE	Pre Regulator									
WDT	Watchdog Timer in SCU-DM									
WDT1	Watchdog Timer in SCU-PM									
WMU	Wake-up Management Unit									
100TP	100 Time Programmable									



Modes of Operation

4 Modes of Operation

This highly integrated circuit contains analog and digital functional blocks. An embedded 32-bit microcontroller is available for system and interface control. On-chip, low-dropout regulators are provided for internal and external power supply. An internal oscillator provides a cost effective clock that is particularly well suited for LIN communications. A LIN transceiver is available as a communication interface. Driver stages for a Motor Bridge or BLDC Motor Bridge with external MOSFET are integrated, featuring PWM capability, protection features and a charge pump for operation at low supply voltage. A 10-bit SAR ADC is implemented for high precision sensor measurement. An 8-bit ADC is used for diagnostic measurements.

The Micro Controller Unit supervision and system protection (including a reset feature) is complemented by a programmable window watchdog. A cyclic wake-up circuit, supply voltage supervision and integrated temperature sensors are available on-chip.

All relevant modules offer power saving modes in order to support automotive applications connected to terminal 30. A wake-up from power-save mode is possible via a LIN bus message, via the monitoring input or using a programmable time period (cyclic wake-up).

Featuring LTI, the integrated circuit is available in a VQFN-48-31 package with 0.5 mm pitch, and is designed to withstand the severe conditions of automotive applications.

The TLE9877QXA20 has several operation modes mainly to support low power consumption requirements.

Reset Mode

The Reset Mode is a transition mode used e.g. during power-up of the device after a power-on reset, or after wakeup from Sleep Mode. In this mode, the on-chip power supplies are enabled and all other modules are initialized. Once the core supply VDDC is stable, the device enters Active Mode. If the watchdog timer WDT1 fails more than four times, the device performs a fail-safe transition to Sleep Mode.

Active Mode

In Active Mode, all modules are activated and the TLE9877QXA20 is fully operational.

Stop Mode

Stop Mode is one of two major low power modes. The transition to the low power modes is performed by setting the corresponding bits in the mode control register. In Stop Mode the embedded microcontroller is still powered, allowing faster wake-up response times. Wake-up from this mode is possible through LIN bus activity, by using the high-voltage monitoring pin or the corresponding 5V GPIOs.

Stop Mode with Cyclic Wake-Up

The Cyclic Wake-Up Mode is a special operating mode of the Stop Mode. The transition to the Cyclic Wake-Up Mode is done by first setting the corresponding bits in the mode control register followed by the Stop Mode command. In addition to the cyclic wake-up behavior (wake-up after a programmable time period), asynchronous wake events via the activated sources (LIN and/or MON) are available, as in normal Stop Mode.

Sleep Mode

The Sleep Mode is a low-power mode. The transition to the low-power mode is done by setting the corresponding bits in the MCU mode control register or in case of failure, see below. In Sleep Mode the embedded microcontroller power supply is deactivated allowing the lowest system power consumption. A wake-up from this mode is possible by LIN bus activity, the High Voltage Monitor Input pin or Cyclic Wake-up.

Sleep Mode in Case of Failure



Power Management Unit (PMU)

5 Power Management Unit (PMU)

5.1 Features

- System modes control (startup, sleep, stop and active)
- Power management (cyclic wake-up)
- Control of system voltage regulators with diagnosis (overload, short, overvoltage)
- Fail safe mode detection and operation in case of system errors (watchdog fail)
- Wake-up sources configuration and management (LIN, MON, GPIOs)
- System error logging

5.2 Introduction

The power management unit is responsible for generating all required voltage supplies for the embedded MCU (VDDC, VDDP) and the external supply (VDDEXT). The power management unit is designed to ensure fail-safe behavior of the system IC by controlling all system modes including the corresponding transitions. Additionally, the PMU provides well defined sequences for the system mode transitions and generates hierarchical reset priorities. The reset priorities control the reset behavior of all system functionalities especially the reset behavior of the embedded MCU. All these functions are controlled by a state machine. The system master functionality of the PMU make use of an independent logic supply and system clock. For this reason, the PMU has an "Internal logic supply and system clock" module which works independently of the MCU clock.



TLE9877QXA20

Power Management Unit (PMU)

Mod. Name	Modules	Functions
Power Supply Generation Unit (PGU)	Voltage regulators for VDDP and VDDC	This block includes the voltage regulators for the pad supply (VDDP) and the core supply (VDDC).
VDDEXT	Voltage regulator for VDDEXT to supply external modules (e.g. sensors)	This voltage regulator is a dedicated supply for external modules and can also be used for cyclic sense operations (e.g. with hall sensor).
PMU-SFR	All Extended Special Function registers that are relevant to the PMU.	This module contains all registers needed to control and monitor the PMU.
PMU-PCU	Power Control Unit of the PMU	This block is responsible for controlling all power related actions within the PGU Module. It also contains all regulator related diagnostics such as undervoltage and overvoltage detection as well as overcurrent and short circuit diagnostics.
PMU-WMU	Wake-Up Management Unit of the PMU	This block is responsible for controlling all wake-up related actions within the PMU Module.
PMU-CMU	Cyclic Management Unit of the PMU	This block is responsible for controlling all actions in cyclic mode.
PMU-RMU	Reset Management Unit of the PMU	This block generates resets triggered by the PMU such as undervoltage or short circuit reset, and passes all resets to the relevant modules and their register.

Table 4 Description of PMU Submodules (cont'd)



ARM Cortex-M3 Core

8 ARM Cortex-M3 Core

8.1 Features

The key features of the Cortex-M3 implemented are listed below.

Processor Core; a low gate count core, with low latency interrupt processing:

- A subset of the Thumb[®]-2 Instruction Set
- Banked stack pointer (SP) only
- 32-bit hardware divide instructions, SDIV and UDIV (Thumb-2 instructions)
- Handler and Thread Modes
- Thumb and debug states
- Interruptible-continued instructions LDM/STM, Push/Pop for low interrupt latency
- · Automatic processor state saving and restoration for low latency Interrupt Service Routine (ISR) entry and exit
- ARM architecture v7-M Style BE8/LE support
- ARMv6 unaligned accesses

Nested Vectored Interrupt Controller (NVIC) closely integrated with the processor core to achieve low latency interrupt processing:

- Interrupts, configurable from 1 to 16
- Bits of priority (4)
- Dynamic reprioritization of interrupts
- Priority grouping. This enables selection of preemptive interrupt levels and non-preemptive interrupt levels
- Support for tail-chaining and late arrival of interrupts. This enables back-to-back interrupt processing without the overhead of state saving and restoration between interrupts.
- Processor state automatically saved on interrupt entry, and restored on interrupt exit, with no instruction
 overhead

Bus interfaces

- Advanced High-performance Bus-Lite (AHB-Lite) interfaces: ICode, DCode, and System bus interface
- Memory access alignment
- Write buffer for buffering of write data



DMA Controller

9.2 Introduction

Please also refer to Chapter 9.3, Functional Description.

9.2.1 Block Diagram



Figure 13 DMA Controller Top Level Block Diagram



GPIO Ports and Peripheral I/O

14 GPIO Ports and Peripheral I/O

The TLE9877QXA20 has 15 port pins organized into three parallel ports: Port 0 (P0), Port 1 (P1) and Port 2 (P2). Each port pin has a pair of internal pull-up and pull-down devices that can be individually enabled or disabled. P0 and P1 are bidirectional and can be used as general purpose input/output (GPIO) or to perform alternate input/output functions for the on-chip peripherals. When configured as an output, the open drain mode can be selected. On Port 2 (P2) analog inputs are shared with general purpose input.

14.1 Features

Bidirectional Port Features (P0, P1)

- Configurable pin direction
- Configurable pull-up/pull-down devices
- Configurable open drain mode
- Configurable drive strength
- Transfer of data through digital inputs and outputs (general purpose I/O)
- Alternate input/output for on-chip peripherals

Analog Port Features (P2)

- Configurable pull-up/pull-down devices
- Transfer of data through digital inputs
- Alternate inputs for on-chip peripherals

14.2 Introduction

14.2.1 Port 0 and Port 1

Figure 17 shows the block diagram of an TLE9877QXA20 bidirectional port pin. Each port pin is equipped with a number of control and data bits, thus enabling very flexible usage of the pin. By defining the contents of the control register, each individual pin can be configured as an input or an output. The user can also configure each pin as an open drain pin with or without internal pull-up/pull-down device.

Each bidirectional port pin can be configured for input or output operation. Switching between input and output mode is accomplished through the register Px_DIR (x = 0 or 1), which enables or disables the output and input drivers. A port pin can only be configured as either input or output mode at any one time.

In input mode (default after reset), the output driver is switched off (high-impedance). The voltage level present at the port pin is translated into a logic 0 or 1 via a Schmitt trigger device and can be read via the register Px_DATA.

In output mode, the output driver is activated and drives the value supplied through the multiplexer to the port pin. In the output driver, each port line can be switched to open drain mode or normal mode (push-pull mode) via the register Px_OD.

The output multiplexer in front of the output driver enables the port output function to be used for different purposes. If the pin is used for general purpose output, the multiplexer is switched by software to the data register Px_DATA . Software can set or clear the bit in Px_DATA and therefore directly influence the state of the port pin. If an on-chip peripheral uses the pin for output signals, alternate output lines (AltDataOut) can be switched via the multiplexer to the output driver circuitry. Selection of the alternate output function is defined in registers $Px_ALTSEL0$ and $Px_ALTSEL1$. When a port pin is used as an alternate function, its direction must be set accordingly in the register Px_DIR .



GPIO Ports and Peripheral I/O

14.3.2 Port 1

14.3.2.1 Port 1 Functions

Table 9 Port 1 Input / Output Functions

Port Pin	Input/Output	Select	Connected Signal(s)	From/to Module	
P1.0	Input	GPI	P1_DATA.P0		
		INP1	T3INC	GPT12T3	
		INP2	T4EUDB	GPT12T4	
		INP3	CC61_0	CCU6	
		INP4	SCK_2	SSC2	
		INP5	EXINT1_2	SCU	
	Output	GPO	P1_DATA.P0		
		ALT1	SCK_2	SSC2	
		ALT2	CC61_0	CCU6	
		ALT3	EXF21_3	Timer 21	
P1.1	Input	GPI	P1_DATA.P1		
		INP1	-	-	
		INP2	T6EUDA	GPT12T6	
		INP3	-	-	
		INP4	MTSR_2	SSC2	
		INP5	T21_1	Timer 21	
		INP6	EXINT1_0	SCU	
	Output	GPO	P1_DATA.P1	-	
		ALT1	MTSR_2	SSC2	
		ALT2	COUT61_0	CCU6	
		ALT3	TXD2_0	UART2	
P1.2	Input	GPI	P1_DATA.P2		
		INP1	T2INA	GPT12T2	
		INP2	T2EX_1	Timer 2	
		INP3	T21EX_3	Timer 21	
		INP4	MRST_2_0	SSC2	
		INP5	RXD2_0	UART2	
		INP6	CCPOS2_2	CCU6	
		INP7	EXINT0_1	SCU	
	Output	GPO	P1_DATA.P2		
		ALT1	MRST_2_0	SSC2	
		ALT2	COUT63_0	CCU6	
		ALT3	T3OUT	GPT12T3	

Capture/Compare Unit 6 (CCU6)

18 Capture/Compare Unit 6 (CCU6)

18.1 Feature Set Overview

This section gives an overview over the different building blocks and their main features.

Timer 12 Block Features

- Three capture/compare channels, each channel can be used either as capture or as compare channel
- Generation of a three-phase PWM supported (six outputs, individual signals for high-side and low-side switches)
- 16-bit resolution, maximum count frequency = peripheral clock
- Dead-time control for each channel to avoid short-circuits in the power stage
- Concurrent update of T12 registers
- · Center-aligned and edge-aligned PWM can be generated
- Single-shot mode supported
- Start can be controlled by external events
- Capability of counting external events
- Multiple interrupt request sources
- Hysteresis-like control mode

Timer 13 Block Features

- One independent compare channel with one output
- 16-bit resolution, maximum count frequency = peripheral clock
- Concurrent update of T13 registers
- Can be synchronized to T12
- Interrupt generation at period-match and compare-match
- Single-shot mode supported
- Start can be controlled by external events
- Capability of counting external events

Additional Specific Functions

- Block commutation for brushless DC-drives implemented
- · Position detection via hall-sensor pattern
- Noise filter supported for position input signals
- Automatic rotational speed measurement and commutation control for block commutation
- Integrated error handling
- Fast emergency stop without CPU load via external signal (CTRAP)
- Control modes for multi-channel AC-drives
- Output levels can be selected and adapted to the power stage

18.2 Introduction

The CCU6 unit is made up of a Timer T12 block with three capture/compare channels and a Timer T13 block with one compare channel. The T12 channels can independently generate PWM signals or accept capture triggers, or they can jointly generate control signal patterns to drive DC-motors or inverters.

A rich set of status bits, synchronized updating of parameter values via shadow registers, and flexible generation of interrupt request signals provide efficient software-control.



Capture/Compare Unit 6 (CCU6)

Note: The capture/compare module itself is referred to as CCU6 (capture/compare unit 6). A capture/compare channel inside this module is referred to as CC6x.

The timer T12 can work in capture and/or compare mode for its three channels. The modes can also be combined (e.g. a channel works in compare mode, whereas another channel works in capture mode). The timer T13 can work in compare mode only. The multi-channel control unit generates output patterns which can be modulated by T12 and/or T13. The modulation sources can be selected and combined for the signal modulation.

18.2.1 Block Diagram



Figure 21 CCU6 Block Diagram



Bridge Driver (incl. Charge Pump)

26 Bridge Driver (incl. Charge Pump)

26.1 Features

The MOSFET Driver is intended to drive external normal level NFET transistors in bridge configuration. The driver provides many diagnostic possibilities to detect faults.

Functional Features

- External Power NFET Transistor Driver Stage with driver capability for max. 100 nC gate charge @ 25 kHz switching frequency.
- Implemented adjustable cross conduction protection.
- Supply voltage (VSD) monitoring incl. adjustable over- and undervoltage shutdown with configurable interrupt signalling.
- VSD operating range down to 5.4 V
- · VDS comparators for short circuit detection in on- and off-state
- Open-Load detection in off-state
- Flexible PWM frequency range, rates above 25 kHz require power dissipation and duty cycle resolution analysis

26.2 Introduction

The MOSFET Driver Stage can be used for controlling external Power NFET Transistors (normal level). The module output is controlled by SFR or System PWM Machine (CCU6).





TLE9877QXA20

- 5) The absolute voltage value is the sum of parameters V_{DDEXT} + $\Delta V_{\text{DDEXTSTB}}$.
- 6) When the condition is met, the Bit VDDEXT_CTRL.bit.SHORT will be set.



6) The given values are worst-case values. In production tests, this leakage current is only tested at 150°C; other values are ensured by correlation. For derating, please refer to the following descriptions:
Leakage derating depending on temperature (T = iunction temperature [°C]):

Leakage derating depending on temperature (T_J = junction temperature [°C]): $I_{OZ} = 0.05 \times e^{(1.5 + 0.028 \times TJ)}$ [µA]. For example, at a temperature of 95°C the resulting leakage current is 3.2 µA.

Leakage derating depending on voltage level (DV = $V_{\text{DDP}} - V_{\text{PIN}}$ [V]):

 $I_{OZ} = I_{OZtempmax} - (1.6 \times DV) [\mu A]$

This voltage derating formula is an approximation which applies for maximum temperature.

7) Keep current: Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: $V_{\text{PIN}} \ge V_{\text{IH}}$ for a pull-up; $V_{\text{PIN}} \le V_{\text{IL}}$ for a pull-down.

Force current: Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device: $V_{\text{PIN}} \le V_{\text{IL}}$ for a pull-up; $V_{\text{PIN}} \ge V_{\text{IH}}$ for a pull-down.

These values apply to the fixed pull-devices in dedicated pins and to the user-selectable pull-devices in general purpose IO pins.

29.5.3 DC Parameters of Port 2

These parameters apply to the IO voltage range, 4.5 V $\leq V_{\text{DDP}} \leq$ 5.5 V.

Note: Operating Conditions apply.

Keeping signal levels within the limits specified in this table ensures operation without overload conditions. For signal levels outside these specifications, also refer to the specification of the overload current I_{OV} .

Table 32DC Characteristics Port 2

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Values		Unit	Note /	Number
		Min.	Тур.	Max.		Test Condition	
Input low voltage	V _{IL}	-0.3	-	0.3 x V _{DDP}	V	$^{1)}4.5V \le V_{DDP} \le$ 5.5V	P_5.2.1
Input low voltage	V_{IL_extend}	-0.3	0.42 x V _{DDP}	-	V	${}^{2)}2.6V \le V_{DDP} \le 4.5V$	P_5.2.10
Input high voltage	V _{IH}	0.7 x V _{DDP}	-	V _{DDP} + 0.3	V	$^{1)}4.5V \le V_{DDP} \le$ 5.5V	P_5.2.2
Input high voltage	V_{IH_extend}	-	0.52 x V _{DDP}	V _{DDP} + 0.3	V	$^{2)}2.6V \le V_{DDP} \le 4.5V$	P_5.2.11
Input hysteresis	HYS _{P2}	0.11 x V _{DDP}	-	_	V	²⁾ Series resistance = 0 Ω; $4.5V \le V_{DDP} \le$ 5.5V	P_5.2.3
Input hysteresis	HYS _{P2_ext}	_	0.09 x V _{DDP}	-	V	²⁾ Series resistance = 0 Ω; 2.6V \leq VDDP $<$ 4.5V	P_5.2.12
Input leakage current	I _{OZ2}	-400	-	+400	nA	$T_{\rm J} \le 85^{\circ}{ m C},$ 0 V < $V_{\rm IN} < V_{\rm DDP}$	P_5.2.4
Pull level keep current	I _{PLK}	-30	-	+30	μA		P_5.2.5



Table 32 DC Characteristics Port 2 (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values				Note /	Number
		Min.	Тур.	Max.		Test Condition	
Pull level force current	I _{PLF}	-750	-	+750	μA	$^{3)} V_{\text{PIN}} \leq V_{\text{IL}} (\text{up})$ $V_{\text{PIN}} \geq V_{\text{IH}} (\text{dn})$	P_5.2.6
Pin capacitance (digital inputs/outputs)	C _{IO}	-	-	10	pF	2)	P_5.2.7

1) Tested at V_{DDP} = 5V, specified for 4.5V < V_{DDP} < 5.5V.

2) Not subject to production test, specified by design.

3) Keep current: Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: $V_{PIN} \ge V_{IH}$ for a pull-up; $V_{PIN} \le V_{IL}$ for a pull-down. Force current: Drive the indicated minimum current through this pin to change the default pin level driven by the enabled

Force current: Drive the indicated minimum current through this pin to change the default pin level driven by th pull device: $V_{\text{PIN}} \le V_{\text{IL}}$ for a pull-up; $V_{\text{PIN}} \ge V_{\text{IH}}$ for a pull-down.



Table 33 Electrical Characteristics LIN Transceiver (cont'd)

 $V_{\rm s}$ = 5.5V to 18V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Bus short circuit current	I _{BUS,sc}	40	100	150	mA	Current Limitation for driver dominant state driver on V_{BUS} = 18 V; LIN Spec 2.2 (Par. 12)	P_6.1.10
Bus short circuit filter time	t _{BUS,sc}	-	5	-	μs	⁶⁾ The overall bus short circuit filter time is a sum of tBUS,sc + digital filter time. The digital filter time is 4 μ s (typ.)	P_6.1.71
Leakage current (loss of ground)	I _{BUS_NO_} gnd	-1000	-450	1000	μA	$V_{\rm S}$ = 12 V; 0 < $V_{\rm BUS}$ < 18 V; LIN Spec 2.2 (Par. 15)	P_6.1.11
Leakage current	I _{BUS_NO_} bat	-	10	20	μA	$V_{\rm S}$ = 0 V; $V_{\rm BUS}$ = 18 V; LIN Spec 2.2 (Par. 16)	P_6.1.12
Leakage current	I _{BUS_PAS} _dom	-1	-	-	mA	$V_{\rm S}$ = 18 V; $V_{\rm BUS}$ = 0 V; LIN Spec 2.2 (Par. 13)	P_6.1.13
Leakage current	I _{BUS_PAS} _rec	-	-	20	μA	$V_{\rm S}$ = 8 V; $V_{\rm BUS}$ = 18 V; LIN Spec 2.2 (Par. 14)	P_6.1.14
Bus pull-up resistance	R _{BUS}	20	30	47	kΩ	Normal mode LIN Spec 2.2 (Par. 26)	P_6.1.15
AC Characteristics - Trans	ceiver No	rmal Slo	ope Mode)			
Propagation delay bus dominant to RxD LOW	t _{d(L),R}	0.1	-	6	μs	LIN Spec 2.2 (Param. 31)	P_6.1.16
Propagation delay bus recessive to RxD HIGH	$t_{\rm d(H),R}$	0.1	-	6	μs	LIN Spec 2.2 (Param. 31)	P_6.1.17
Receiver delay symmetry	t _{sym,R}	-2	-	2	μs	$t_{\text{sym,R}} = t_{d(L),R} - t_{d(H),R};$ LIN Spec 2.2 (Par. 32)	P_6.1.18
Duty cycle D1 Normal Slope Mode (for worst case at 20 kbit/s)	t _{duty1}	0.396	_	-		⁴⁾ duty cycle 1 $TH_{Rec}(max) =$ $0.744 \times V_S;$ $TH_{Dom}(max) =$ $0.581 \times V_S; V_S = 5.5$ 18 V; $t_{bit} = 50 \ \mu s;$ $D1 = t_{bus_rec(min)}/2 \ t_{bit};$ LIN Spec 2.2 (Par. 27)	P_6.1.19



29.7 High-Speed Synchronous Serial Interface

29.7.1 SSC Timing Parameters

The table below provides the SSC timing in the TLE9877QXA20.

Table 34 SSC Master Mode Timing (Operating Conditions apply; CL = 50 pF)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Values		Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
SCLK clock period	t ₀	¹⁾ 2 * T _{SSC}	-	_		²⁾ $V_{\rm DDP}$ > 2.7 V	P_7.1.1
MTSR delay from SCLK	<i>t</i> ₁	10	-	_	ns	²⁾ $V_{\rm DDP}$ > 2.7 V	P_7.1.2
MRST setup to SCLK	<i>t</i> ₂	10	-	_	ns	²⁾ $V_{\rm DDP}$ > 2.7 V	P_7.1.3
MRST hold from SCLK	<i>t</i> ₃	15	-	-	ns	²⁾ $V_{\rm DDP}$ > 2.7 V	P_7.1.4

1) $T_{SSCmin} = T_{CPU} = 1/f_{CPU}$. If $f_{CPU} = 20$ MHz, $t_0 = 100$ ns. T_{CPU} is the CPU clock period.

2) Not subject to production test, specified by design.



Figure 37 SSC Master Mode Timing



Table 42 Electrical Characteristics MOSFET Driver (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Values			Note / Test Condition	Number
		Min.	Тур.	Max.			
High level output voltage GLx vs. GND	V _{Gxx6}	8	_	-	V	$V_{\rm SD}$ = 6.4 V ¹⁾ , $C_{\rm Load}$ = 10 nF, $I_{\rm CP}$ =2.5 mA ²⁾	P_12.1.6
High level output voltage GLx vs. GND	V _{Gxx7}	7	-	-	V	$V_{\rm SD}$ = 5.4 V, $C_{\rm Load}$ = 10 nF, $I_{\rm CP}$ =2.5 mA ²⁾	P_12.1.7
Rise time	t _{rise3_3nf}	-	200	_	ns	¹⁾ CLoad = 3.3 nF, $V_{SD} \ge 8 V$, 25-75% of V_{Gxx1} , $I_{CHARGE} = I_{DISCHG} = 31(max)$	P_12.1.8
Fall time	t _{fall3_3nf}	_	200	_	ns	$\label{eq:Load} {}^{1)}C_{\text{Load}} = 3.3 \text{ nF}, \\ V_{\text{SD}} \geq 8 \text{ V}, \\ 75\text{-}25\% \text{ of } V_{\text{Gxx1}}, I_{\text{CHARGE}} = \\ I_{\text{DISCHG}} = 31(\text{max}) \\ \end{array}$	P_12.1.9
Rise time	t _{risemax}	100	250	450	ns	$\begin{array}{l} C_{\rm Load} = 10 \ {\rm nF}, \\ V_{\rm SD} \geq 8 \ {\rm V}, \\ 25\text{-}75\% \ {\rm of} \ V_{\rm Gxx1}, I_{\rm CHARGE} = \\ I_{\rm DISCHG} = 31({\rm max}) \end{array}$	P_12.1.57
Fall time	t _{fallmax}	100	250	450	ns	$\begin{split} C_{\text{Load}} &= 10 \text{ nF}, \\ V_{\text{SD}} \geq 8 \text{ V}, \\ \textbf{75-25\% of } V_{\text{Gxx1}}, I_{\text{CHARGE}} = \\ I_{\text{DISCHG}} &= \textbf{31}(\text{max}) \end{split}$	P_12.1.58
Rise time	<i>t</i> _{risemin}	1.25	2.5	5	μs	$^{1)}C_{\text{Load}} = 10 \text{ nF},$ $V_{\text{SD}} \ge 8 \text{ V},$ 25-75% of $V_{\text{Gxx1}},$ $I_{\text{CHARGE}} = I_{\text{DISCHG}} = 3(\text{min})$	P_12.1.14
Fall time	t _{fallmin}	1.25	2.5	5	μs	¹⁾ C_{Load} = 10 nF, $V_{\text{SD}} \ge 8 \text{ V},$ 75-25% of $V_{\text{Gxx1}},$ I_{CHARGE} = I_{DISCHG} = 3(min)	P_12.1.15
Absolute rise - fall time difference for all LSx	<i>t</i> _{r_f(diff)LSx}	-	-	100	ns	$\begin{array}{l} C_{\rm Load} = 10 \; \rm nF, \\ V_{\rm SD} \geq 8 \; \rm V, \\ 25\text{-}75\% \; \rm of \; V_{\rm Gxx1}, I_{\rm CHARGE} = \\ I_{\rm DISCHG} = 31(\rm max) \end{array}$	P_12.1.35
Absolute rise - fall time difference for all HSx	t _{r_f(diff)HSx}	_	-	100	ns	$\begin{array}{l} C_{\text{Load}} = 10 \text{ nF}, \\ V_{\text{SD}} \geq 8 \text{ V}, \\ \text{25-75\% of } V_{\text{Gxx1}}, I_{\text{CHARGE}} = \\ I_{\text{DISCHG}} = 31(\text{max}) \end{array}$	P_12.1.36
Resistor between GHx/GLx and GND	R _{GGND}	30	40	50	kΩ	1)	P_12.1.11



29.13 Operational Amplifier

29.13.1 Electrical Characteristics

Table 43 Electrical Characteristics Operational Amplifier

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Differential gain (uncalibrated)	G	9.5 19 38 57	10 20 40 60	10.5 21 42 63		Gain settings GAIN<1:0>: 00 01 10 11	P_13.1.6
Differential input operating voltage range OP2 - OP1	V_{IX}	-1.5 / G	-	1.5 / G	V	G is the Gain specified below	P_13.1.1
Operating. common mode input voltage range (referred to GND (OP2 - GND) or (OP1 - GND)	V _{CM}	-2.0	-	2.0	V	Input common mode has to be checked in evaluation if it fits the required range	P_13.1.2
Max. input voltage range (referred to GND (OP_2 - GND) or (OP1 - GND)	V _{IX_max}	-7.0	-	7.0	V	Max. rating of operational amplifier inputs, where measurement is not done	P_13.1.3
Single ended output voltage range (linear range)	V _{OUT}	V _{ZERO} - 1.5	-	V _{ZERO} + 1.5	V	¹⁾²⁾ typ. output offset voltage 2 V \pm 1.5V	P_13.1.4
Linearity error	E _{PWM}	-15	-	15	mV	Maximum deviation from best fit straight line divided by max. value of differential output voltage range ($0.5V - 3.5V$); this parameter is determined at G = 10.	P_13.1.5
Linearity error	E _{PWM_%}	-1.0	-	1.0	%	Maximum deviation from best fit straight line divided by max. value of differential output voltage range (0.5V - 3.5V); this parameter is determined at G = 10.	P_13.1.24
Gain drift		-1	-	1	%	Gain drift after calibration at $G = 10$.	P_13.1.7
Adjusted output offset voltage	V _{oos}	-40	10	40	mV	$V_{\text{AIP}} = V_{\text{AIN}} = 0 \text{ V} \text{ and}$ G = 40.	P_13.1.17



Table 43 Electrical Characteristics Operational Amplifier (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
DC input voltage common mode rejection ratio	DC- CMRR	58	80	-	dB	CMRR (in dB)=-20*log (differential mode gain/ common mode gain) V_{CMI} = -2V 2V, V_{AIP} - V_{AIN} =0V	P_13.1.8
Settling time to 98%	T _{SET}	-	800	1400	ns	Derived from 80 - 20 % rise fall times for \pm 2V overload condition (3 Tau value of settling time constant) ²	P_13.1.9
Current Sense Amplifier Input Resistance @ OP1, OP2	R _{in_OP1_} 0P2	1	1.25	1.5	kΩ	2)	P_13.1.25



Package Outlines

30 Package Outlines



Figure 38 Package outline VQFN-48-31 (with LTI)

Notes

- 1. You can find all of our packages, sorts of packing and others in our Infineon Internet Page "Products": http://www.infineon.com/products.
- 2. Dimensions in mm.